

YJ Planar Schottky Barrier Diode Die Specification

60V 2A, 40mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB040M060SS-280A

Main Products Characterstics

Maximum Ratings

	Rating
Repetitive peak reverse voltage	60 V
Average forward current	2 A

Static Electrical Characteristics (Ta = 25°C)

Parameter	Symbol
Reverse breakdown voltage	V_{BR}
Reverse leakage current	$I_R = 1mA$
Maximum reverse current	I_R

Device Schematics and Outline Drawing

- Die Thickness *
- Die Size ** 40 Mils
- Top Metal Pad
- Active Area
- Top Metal
- Back Metal Ag
- Note: 1 * : Also can offer device with 8 mils thickness
- 2 **: Cutting street width is around 1.5 mils

Important Notice

- Specification apply to die only. Actual performance may degrade when assembled.

YangjieElectronics does not guarantee device performance after assembly.
All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.
- Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.